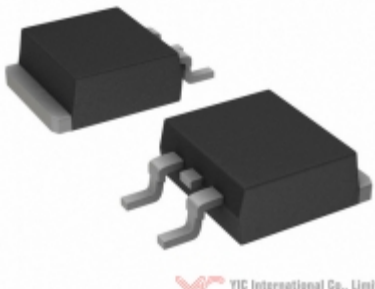







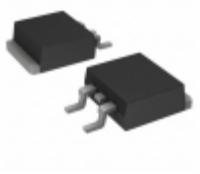

	<h2 style="color: red;">HGT1S10N120BNST</h2>	
	Hersteller-Teilenummer:	HGT1S10N120BNST
	Hersteller / Marke:	AMI Semiconductor / ON Semiconductor
	Teil der Beschreibung:	IGBT 1200V 35A 298W TO263AB
Datenblätter:	 HGT1S10N120BNST.pdf	
RoHs Status:	Bleifrei / RoHS-konform	
Lagerzustand:	New original, 2214 pcs Stock Available.	
Liefern von:	Hong Kong	
Versandweg:	DHL/Fedex/TNT/UPS/EMS	
<p>Image may be representation. See specs for product details.</p>		

Spezifikationen

Teilenummer	HGT1S10N120BNST
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	IGBT 1200V 35A 298W TO263AB
Kategorie	Diskrete Halbleiterprodukte > Transistoren-IGBTs-
Teilstatus	2214 pcs Stock
Hersteller Standard Vorlaufzeit	44 Weeks
detaillierte Beschreibung	IGBT NPT 1200V 35A 298W Surface Mount TO-263AB
Serie	-
Eingabetyp	Standard
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	298W
Verpackung / Gehäuse	TO-263-3, D ² Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	TO-263AB
Strom - Kollektor (Ic) (max)	35A
Spannung - Kollektor-Emitter-Durchbruch (max)	1200V
IGBT-Typ	NPT
VCE (on) (Max) @ Vge, Ic	2.7V @ 15V, 10A
Strom - Collector Pulsed (Icm)	80A
Schaltenergie	320µJ (on), 800µJ (off)
Gate-Ladung	100nC
Td (ein / aus) bei 25 ° C	23ns/165ns
Testbedingung	960V, 10A, 10 Ohm, 15V
Verpackung	Tape & Reel (TR)
Basisteilenummer	HGT1S10N120
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	HGT1S10N120BNST-ND

HGT1S10N120BNST ist neu im Original, Suche HGT1S10N120BNST Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie HGT1S10N120BNST AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage HGT1S10N120BNST: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>HGT1S10N120BNS AMI Semiconductor / ON Semiconductor IGBT 1200V 35A 298W TO263AB</p>	 <p>HGT1N40N60A4D Fairchild/ON Semiconductor IGBT SMPS N-CHAN 600V SOT-227</p>	 <p>HGT1S12N60C3 HARRIS HGT1S12N60C3 HARRIS</p>	 <p>HGT1S12N60A4S9A Fairchild/ON Semiconductor IGBT 600V 54A 167W TO263AB</p>
 <p>HGT1S12N60A4DS AMI Semiconductor / ON Semiconductor IGBT 600V 54A 167W D2PAK</p>	 <p>HGT1N40N60A4D AMI Semiconductor / ON Semiconductor IGBT SMPS N-CHAN 600V SOT-227</p>	 <p>HGT1S12N60A4S9A AMI Semiconductor / ON Semiconductor IGBT 600V 54A 167W TO263AB</p>	 <p>HGT1S10N120BNST Fairchild/ON Semiconductor IGBT 1200V 35A 298W TO263AB</p>

heiße Teile

Mehr

<ul style="list-style-type: none"> ⊕ HGT1N30N60A4 ⊖ HGT1S12N60C3 ⊕ HGT1S14N41G3VL29A D HGT1S20N36G3VLSR4737 ⇒ HGT1S2N120CN ⇒ HGT1S3N60B3DS ⊕ HGT1S7N60A4DS9A ⊖ HGT1S7N60C3DS9A ⊕ HGTG10N120BND ⇒ HGTG12N60A4 	<ul style="list-style-type: none"> ⇒ HGT1N40N60A4 ⊕ HGT1S12N60C3DS ⊖ HGT1S14N41G3VLS9A ⊕ HGT1S20N60A4S9A ⇒ HGT1S2N120CN ⇒ HGT1S3N60C3DS9A D HGT1S7N60A4S9A ⊕ HGT1S7N60C3DS9A ⊖ HGTG11N120CN ⊕ HGTG12N60A4 	<ul style="list-style-type: none"> ⇒ HGT1S10N120BNS D HGT1S12N60C3DS9A ⊕ HGT1S15N120C3ST ⊖ HGT1S20N60A4S9A ⊕ HGT1S3N60A4DS D HGT1S7N60A4DS ⇒ HGT1S7N60B3 ⇒ HGTD1N120BNS9A ⊕ HGTG11N120CN ⊖ HGTG12N60A4D 	<ul style="list-style-type: none"> D HGT1S10N120BNS ⇒ HGT1S12N60C3S ⇒ HGT1S1N120CNDST ⊕ HGT1S20N60C3R ⊖ HGT1S3N60A4DS9A ⊕ HGT1S7N60A4DS ⇒ HGT1S7N60B3DS ⇒ HGTD1N120BNS9A D HGTG11N120CND ⊕ HGTG12N60A4D 	<ul style="list-style-type: none"> ⇒ HGT1S10N120BNST ⇒ HGT1S14N40G3VLS ⇒ HGT1S20N36G3VLS ⇒ HGT1S20N60C3RS ⇒ HGT1S3N60A4DS9A ⊖ HGT1S7N60A4DS.G7N60A4D ⇒ HGT1S7N60B3S ⇒ HGTG10N120BND ⇒ HGTG11N120CND ⇒ HGTG12N60B3D
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Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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